Product data sheet

1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Low threshold voltage
- Low on-state resistance
- Trench MOSFET technology
- Enhanced power dissipation capability of 890 mW
- AEC-Q101 qualified

3. Applications

- Relay driver
- High-speed line driver
- High-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-------------------|----------------------------------|---|-----|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | - | -20 | V |
| V_{GS} | gate-source voltage | | | -8 | - | 8 | V |
| I _D | drain current | $V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}; t \le 5 \text{ s}$ | [1] | - | - | -2.3 | Α |
| Static charact | Static characteristics | | | | | | , |
| R _{DSon} | drain-source on-state resistance | V_{GS} = -4.5 V; I_D = -2 A; T_j = 25 °C | | - | 120 | 170 | mΩ |

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².



20 V, P-channel Trench MOSFET

5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-------------|--------------------|-----------------------|
| 1 | G | gate | 3 | D |
| 2 | S | source | | |
| 3 | D | drain | 1 2 | G S S 017aaa257 |
| | | | TO-236AB (SOT23) | |

6. Ordering information

Table 3. Ordering information

| Type number | Package | | | | |
|-------------|----------|--|---------|--|--|
| | Name | Description | Version | | |
| BSH205G2 | TO-236AB | plastic surface-mounted package; 3 leads | SOT23 | | |

7. Marking

Table 4. Marking codes

| Table II III III II II II II II II II II II | |
|---|--------------|
| Type number | Marking code |
| | បា |
| BSH205G2 | %KB |

^{[1] % =} placeholder for manufacturing site code

20 V, P-channel Trench MOSFET

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | | Min | Max | Unit |
|------------------|-------------------------|---|-----|-----|------|------|
| V _{DS} | drain-source voltage | T _j = 25 °C | | - | -20 | V |
| V _{GS} | gate-source voltage | | | -8 | 8 | V |
| I _D | drain current | V _{GS} = -4.5 V; T _{amb} = 25 °C; t ≤ 5 s | [1] | - | -2.3 | Α |
| | | V _{GS} = -4.5 V; T _{amb} = 25 °C | [1] | - | -2 | Α |
| | | V _{GS} = -4.5 V; T _{amb} = 100 °C | [1] | - | -1.2 | Α |
| I _{DM} | peak drain current | T_{amb} = 25 °C; single pulse; $t_p \le 10$ μs | | - | -8 | Α |
| P _{tot} | total power dissipation | T _{amb} = 25 °C | [2] | - | 480 | mW |
| | | | [1] | - | 890 | mW |
| | | T _{sp} = 25 °C | | - | 6250 | mW |
| Tj | junction temperature | | | -55 | 150 | °C |
| T _{amb} | ambient temperature | | | -55 | 150 | °C |
| T _{stg} | storage temperature | | | -65 | 150 | °C |
| Source-drain o | liode | | | | | |
| Is | source current | T _{sp} = 25 °C | [1] | - | -0.8 | Α |

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².
- [2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

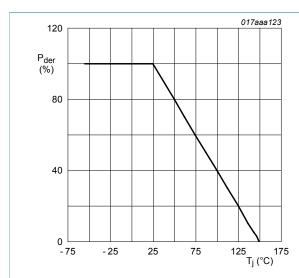


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

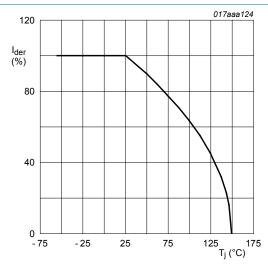


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

BSH205G2

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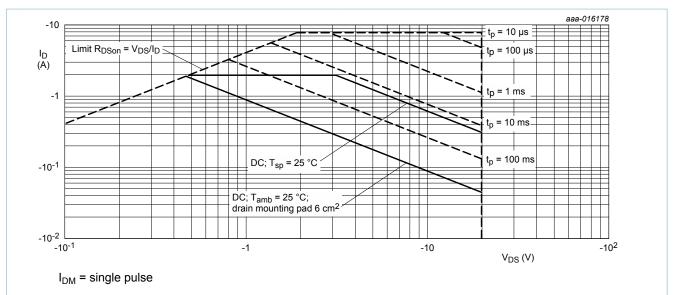


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|-----------------------|--|----------------------|-----|-----|-----|-----|------|
| R _{th(j-a)} | thermal resistance | | [1] | - | 230 | 260 | K/W |
| | from junction to ambient | | [2] | - | 120 | 140 | K/W |
| | ambient | in free air; t ≤ 5 s | [2] | - | 85 | 100 | K/W |
| R _{th(j-sp)} | thermal resistance from junction to solder point | | | - | 15 | 20 | K/W |

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm².

20 V, P-channel Trench MOSFET

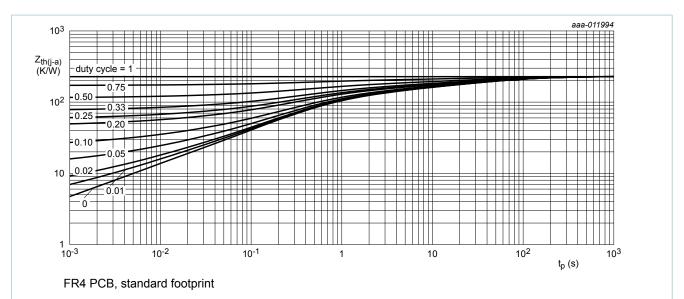


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

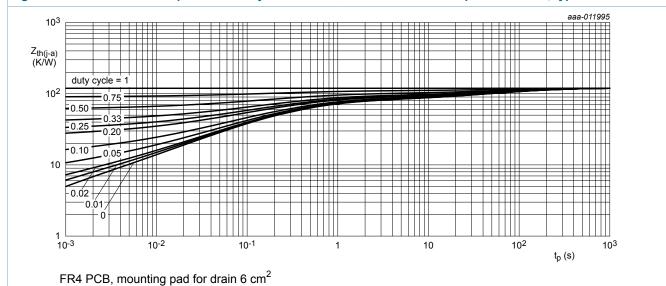


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

20 V, P-channel Trench MOSFET

10. Characteristics

Table 7. Characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------------|-----------------------------------|---|-------|------|-------|------|
| Static char | acteristics | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | I_D = -250 μ A; V_{GS} = 0 V; T_j = 25 °C | -20 | - | - | V |
| V_{GSth} | gate-source threshold voltage | I_D = -250 μ A; V_{DS} = V_{GS} ; T_j = 25 °C | -0.45 | -0.7 | -0.95 | V |
| I _{DSS} | drain leakage current | V_{DS} = -20 V; V_{GS} = 0 V; T_j = 25 °C | - | - | -1 | μA |
| I _{GSS} | gate leakage current | V _{GS} = 8 V; V _{DS} = 0 V; T _j = 25 °C | - | - | 100 | nA |
| | | V _{GS} = -8 V; V _{DS} = 0 V; T _j = 25 °C | - | - | -100 | nA |
| R _{DSon} | drain-source on-state | V_{GS} = -4.5 V; I_D = -2 A; T_j = 25 °C | - | 120 | 170 | mΩ |
| | resistance | V_{GS} = -4.5 V; I_D = -2 A; T_j = 150 °C | - | 168 | 238 | mΩ |
| | | V_{GS} = -2.5 V; I_D = -1.5 A; T_j = 25 °C | - | 150 | 230 | mΩ |
| | | V_{GS} = -1.8 V; I_D = -0.6 A; T_j = 25 °C | - | 200 | 320 | mΩ |
| | | V_{GS} = -1.5 V; I_D = -0.1 A; T_j = 25 °C | - | 260 | 600 | mΩ |
| 9 _{fs} | forward transconductance | V_{DS} = -10 V; I_{D} = -2 A; T_{j} = 25 °C | - | 4.5 | - | S |
| Dynamic c | haracteristics | | | | | |
| Q _{G(tot)} | total gate charge | V_{DS} = -10 V; I_{D} = -2 A; V_{GS} = -4.5 V; | - | 3.7 | 6.5 | nC |
| Q _{GS} | gate-source charge | T _j = 25 °C | - | 0.6 | - | nC |
| Q _{GD} | gate-drain charge | | - | 0.8 | - | nC |
| C _{iss} | input capacitance | V _{DS} = -10 V; f = 1 MHz; V _{GS} = 0 V; | - | 418 | - | pF |
| C _{oss} | output capacitance | T _j = 25 °C | - | 45 | - | pF |
| C _{rss} | reverse transfer capacitance | | - | 34 | - | pF |
| t _{d(on)} | turn-on delay time | V_{DS} = -10 V; I_D = -2 A; V_{GS} = -4.5 V; | - | 5 | - | ns |
| t _r | rise time | $R_{G(ext)} = 6 \Omega; T_j = 25 °C$ | - | 14 | - | ns |
| t _{d(off)} | turn-off delay time | | - | 43 | - | ns |
| t _f | fall time | | - | 16 | - | ns |
| Source-dra | in diode | ı | 1 | 1 | 1 | |
| V _{SD} | source-drain voltage | $I_S = -0.8 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$ | - | -0.8 | -1.2 | V |

20 V, P-channel Trench MOSFET

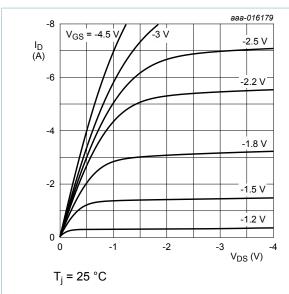


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

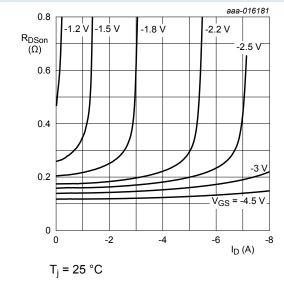


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

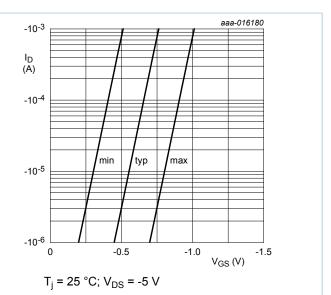


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

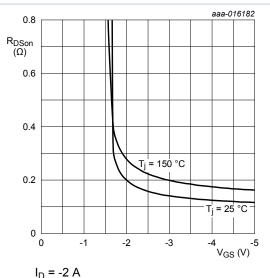


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

20 V, P-channel Trench MOSFET

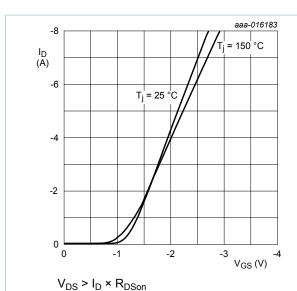


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

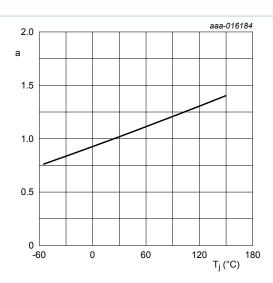


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

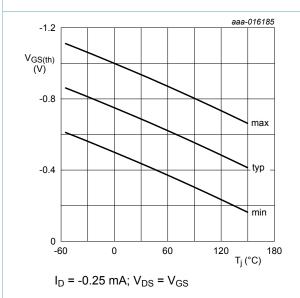


Fig. 12. Gate-source threshold voltage as a function of junction temperature

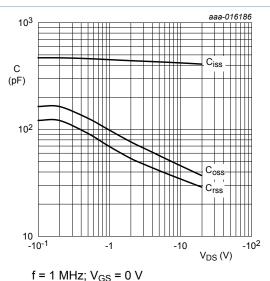


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

20 V, P-channel Trench MOSFET

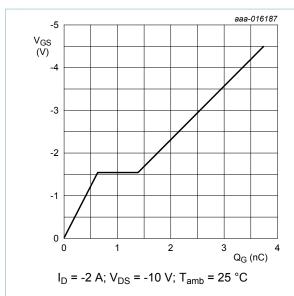


Fig. 14. Gate-source voltage as a function of gate charge; typical values

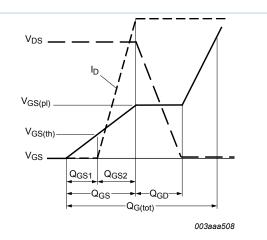


Fig. 15. MOSFET transistor: Gate charge waveform definitions

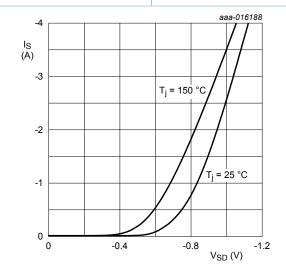
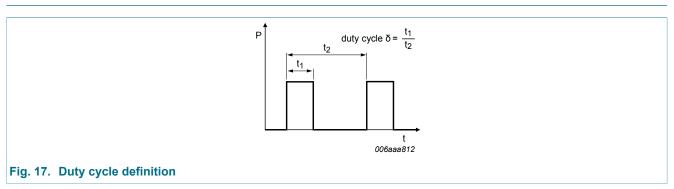


Fig. 16. Source current as a function of source-drain voltage; typical values

11. Test information

 $V_{GS} = 0 V$



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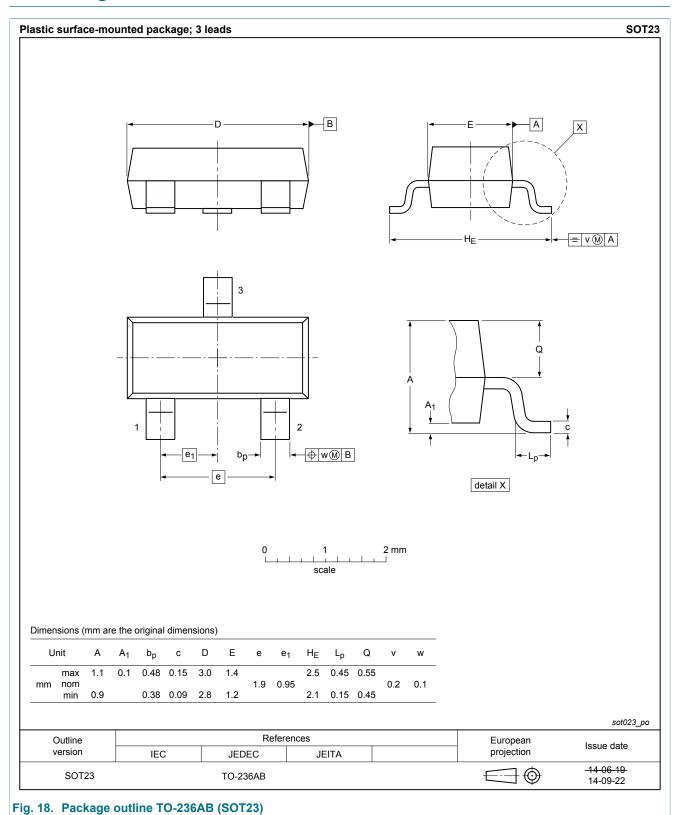
20 V, P-channel Trench MOSFET

11.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

20 V, P-channel Trench MOSFET

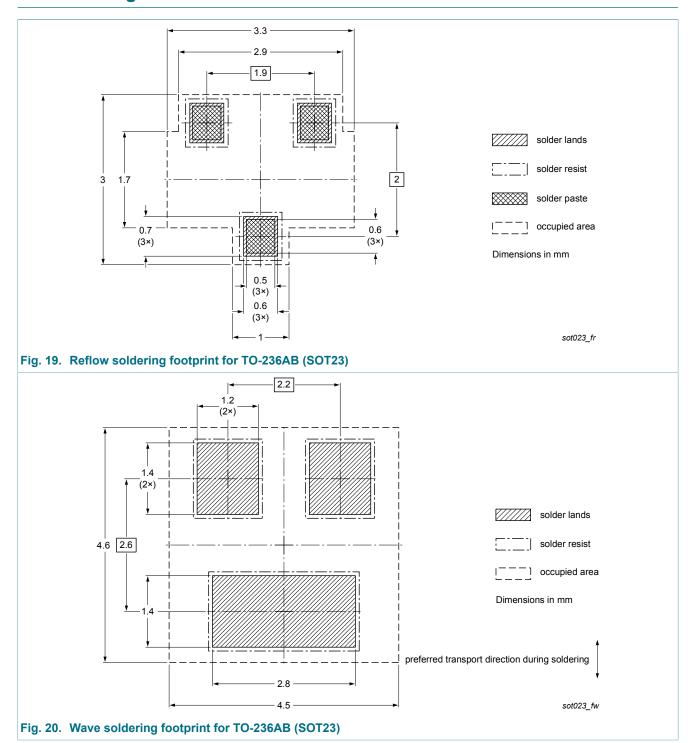
12. Package outline



BSH205G2

20 V, P-channel Trench MOSFET

13. Soldering



20 V, P-channel Trench MOSFET

14. Revision history

Table 8. Revision history

| Data sheet ID | Release date | Data sheet status | Change notice | Supersedes |
|----------------|--------------------|--------------------|---------------|--------------|
| BSH205G2 v. 2 | 20150429 | Product data sheet | - | BSH205G2 v.1 |
| Modifications: | AEC-Q101 qualified | 1 | | |
| BSH205G2 v.1 | 20141215 | Product data sheet | - | - |

20 V, P-channel Trench MOSFET

15. Legal information

15.1 Data sheet status

| Document status [1][2] | Product status [3] | Definition |
|--------------------------------------|--------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
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20 V, P-channel Trench MOSFET

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20 V, P-channel Trench MOSFET

16. Contents

| 1 | General description | 1 |
|------|-------------------------|----|
| 2 | Features and benefits | 1 |
| 3 | Applications | 1 |
| 4 | Quick reference data | 1 |
| 5 | Pinning information | 2 |
| 6 | Ordering information | 2 |
| 7 | Marking | 2 |
| 8 | Limiting values | 3 |
| 9 | Thermal characteristics | 4 |
| 10 | Characteristics | 6 |
| 11 | Test information | 9 |
| 11.1 | Quality information | 10 |
| 12 | Package outline | 11 |
| 13 | Soldering | 12 |
| 14 | Revision history | 13 |
| 15 | Legal information | 14 |
| 15.1 | Data sheet status | 14 |
| 15.2 | Definitions | 14 |
| 15.3 | Disclaimers | 14 |
| 15.4 | Trademarks | 15 |
| | | |

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